

THOMSON

DELPHION
RESEARCH**SERVICES****INSIDE DELPHION**
[Log Out](#) | [Work Files](#) | [Saved Searches](#)
[My Account](#) | [Products](#)
[Search: Quick Number](#) | [Boolean](#) | [Advanced](#)

The Delphion Integrated View

Get Now: ☐ PDF | [More choices...](#)
Tools: [Add to Work File](#) | [Create new Work File](#)
View: [Expand Details](#) | [INPADOC](#) | [Jump to:](#)
[Go to:](#) [Derwent](#)
☐ [Email this](#)
Title: WO0188482A1: SENSOR ELEMENT AND ITS MANUFACTURING METHOD
Country: WO World Intellectual Property Organization (WIPO)

Kind: A1 Publ. of the Int. Appl. with Int. search report

Inventor: YASUDA, Naoki; Mitsubishi Denki Kabushiki Kaisha, 2-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 100-8310, Japan

FUKAMI, Tatsuya; Mitsubishi Denki Kabushiki Kaisha, 2-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 100-8310, Japan

TAGUCHI, Motohisa; Mitsubishi Denki Kabushiki Kaisha, 2-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 100-8310, Japan

KAWANO, Yuji; Mitsubishi Denki Kabushiki Kaisha, 2-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 100-8310, Japan

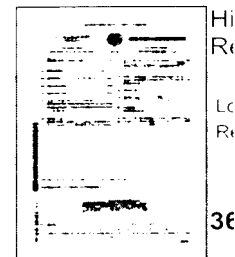
Assignee: MITSUBISHI DENKI KABUSHIKI KAISHA, 2-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 100-8310, Japan

[News, Profiles, Stocks and More about this company](#)
Published / Filed: 2001-11-22 / 2000-05-15
Application Number: WO2000JP0003077
IPC Code: G01D 21/00; H01L 43/12; G01F 1/68; G01P 15/08; G01R 33/06; G01L 9/00; H01L 29/84;
ECLA Code: G01F1/684M;
Priority Number: 2000-05-15 WO2000000003077
Abstract:

A sensor element is provided with a sensor substrate and a sensing portion supported by the substrate, wherein a resin film is formed between the sensor substrate and the sensing member. The resin film has heat resistance against manufacturing process temperatures and use temperatures and excellent coverage of the underlying surface having a three-dimensional structure. The surface can be planarized. The stress on the sensing portion is little. The resin film can be formed at a low temperature, which prevents bad influence on the sensing portion during the manufacturing process.

[\[Show in French\]](#)
Attorney, Agent or Firm: MIYATA, Kaneo ; Mitsubishi Denki Kabushiki Kaisha, 2-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 100-8310 Japan

INPADOC Legal Status: [Show legal status actions](#) **Get Now:** [Family Legal Status Report](#)
Designated Country: JP KR US, **European patent:** AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

Family: [Show 2 known family members](#)
Other Abstract Info: DERABS G2002-139484 DERABS G2002-139484


(12)特許協力条約に基づいて公開された国際出願

(19) 世界知的所有権機関
国際事務局



(43) 国際公開日
2001年11月22日 (22.11.2001)

PCT

(10) 国際公開番号
WO 01/88482 A1

(51) 国際特許分類: G01D 21/00, H01L 43/12, G01F 1/68,
G01P 15/08, G01R 33/06, G01L 9/00, H01L 29/84

[JP/JP] 田口元久 (TAGUCHI, Motohisa) [JP/JP] 川野
裕司 (KAWANO, Yuji) [JP/JP]: 〒100-8310 東京都千代
田区丸の内二丁目2番3号 三菱電機株式会社内 Tokyo
(JP).

(21) 国際出願番号: PCT JP00/03077

(22) 国際出願日: 2000年5月15日 (15.05.2000)

(74) 代理人: 宮田金雄, 外 (MIYATA, Kaneo et al.): 〒
100-8310 東京都千代田区丸の内二丁目2番3号 三菱
電機株式会社内 Tokyo (JP).

(25) 国際出願の言語: 日本語

(81) 指定国 (国内): JP, KR, US.

(26) 国際公開の言語: 日本語

(84) 指定国 (広域): ヨーロッパ特許 (AT, BE, CH, CY, DE,
DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).

(71) 出願人 (米国を除く全ての指定国について): 三
菱電機株式会社 (MITSUBISHI DENKI KABUSHIKI
KAISHA) [JP/JP]: 〒100-8310 東京都千代田区丸の内
二丁目2番3号 Tokyo (JP).

添付公開書類:
— 国際調査報告書

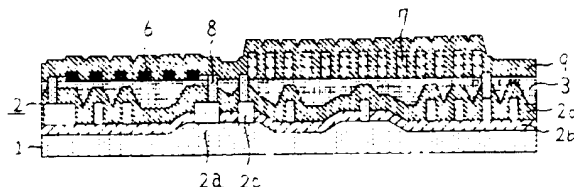
(72) 発明者; および

(75) 発明者/出願人 (米国についてのみ): 保田直紀 (YA-
SUDA, Naoki) [JP/JP] 深見達也 (FUKAMI, Tatsuya)

2文字コード及び他の略語については、定期発行される
各PCTガゼットの巻頭に掲載されている「コードと略語
のガイダンスノート」を参照。

(54) Title: SENSOR ELEMENT AND ITS MANUFACTURING METHOD

(54) 発明の名称: センサ素子及びその製造方法



(57) Abstract: A sensor element is provided with a sensor substrate and a sensing portion supported by the substrate, wherein a resin film is formed between the sensor substrate and the sensing member. The resin film has heat resistance against manufacturing process temperatures and use temperatures and excellent coverage of the underlying surface having a three-dimensional structure. The surface can be planarized. The stress on the sensing portion is little. The resin film can be formed at a low temperature, which prevents bad influence on the sensing portion during the manufacturing process.

[続葉有]

WO 01/88482 A1